IXYS

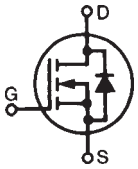
Preliminary Technical Information

X2-Class Power MOSFET

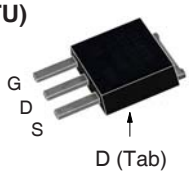
N-Channel Enhancement Mode

IXTU8N70X2
IXTY8N70X2
IXTA8N70X2
IXTP8N70X2

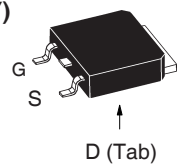
V_{DSS} = 700V
I_{D25} = 8A
$R_{DS(on)}$ ≤ 500mΩ



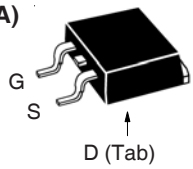
TO-251 (IXTU)



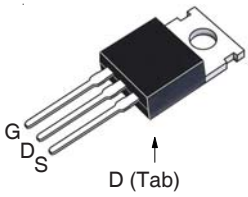
TO-252 (IXTY)



TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	700	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	700	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	8	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	16	A
I_A	T_C = 25°C	4	A
E_{AS}	T_C = 25°C	250	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le$ 150°C	50	V/ns
P_D	T_C = 25°C	150	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
F_C	Mounting Force (TO-263 & TO-251)	10..65 / 2.2..14.6	N/lb
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in
Weight	TO-251	0.40	g
	TO-252	0.35	g
	TO-263	2.50	g
	TO-220	3.00	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA	700			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0		5.0	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±100	nA
I_{DSS}	V_{DS} = V_{DSS}, V_{GS} = 0V			10	μA
	T_J = 125°C			250	μA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 0.5 • I_{D25}, Note 1			500	mΩ

Features

- International Standard Packages
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
g_{fs}	V_{DS} = 10V, I_D = 0.5 • I_{D25}, Note 1	4.8	8.0		S
R_{Gi}	Gate Input Resistance		6		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		800		pF
C_{oss}			495		pF
C_{rss}			2.2		pF
	Effective Output Capacitance				
$C_{o(er)}$	Energy related, V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		43		pF
$C_{o(tr)}$	Time related, V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		129		pF
$t_{d(on)}$	**Resistive Switching Times**		24		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		28		ns
$t_{d(off)}$	R_G = 30Ω (External)		53		ns
t_f			24		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		12.0		nC
Q_{gs}			3.1		nC
Q_{gd}			4.4		nC
R_{thJC}				0.83	°C/W
R_{thCS}	TO-220		0.50		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
I_S	V_{GS} = 0V			8	A
I_{SM}	Repetitive, pulse Width Limited by T_{JM}			32	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 4A, -di/dt = 100A/μs, V_R = 100V		200		ns
Q_{RM}			1.65		μC
I_{RM}			16.3		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065B1 6,683,344 6,727,585 7,005,734B2 7,157,338B2 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123B1 6,534,343 6,710,405B2 6,759,692 7,063,975B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728B1 6,583,505 6,710,463 6,771,478B2 7,071,537

Fig. 1. Output Characteristics @ T_J = 25°C

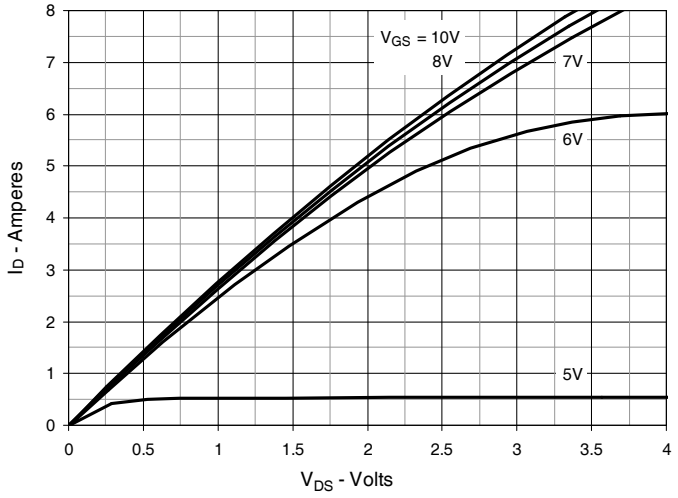

Fig. 2. Extended Output Characteristics @ T_J = 25°C

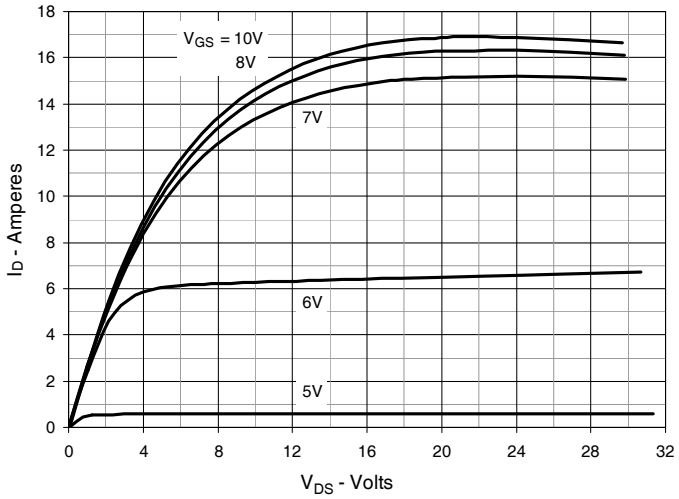

Fig. 3. Output Characteristics @ T_J = 125°C

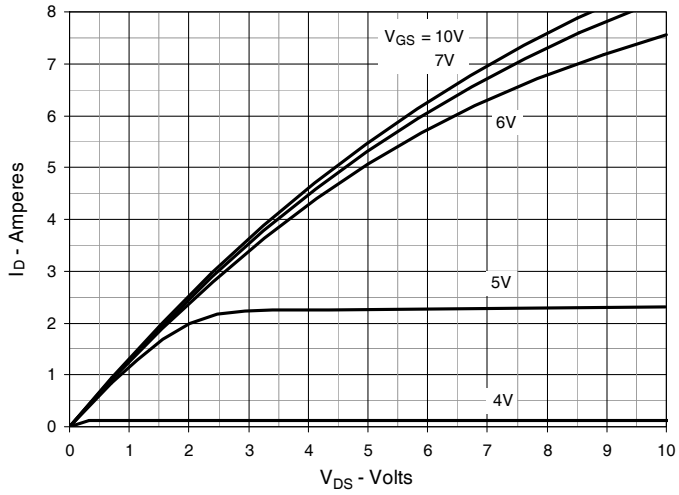

Fig. 4. $R_{DS(on)}$ Normalized to I_D = 4A Value vs. Junction Temperature

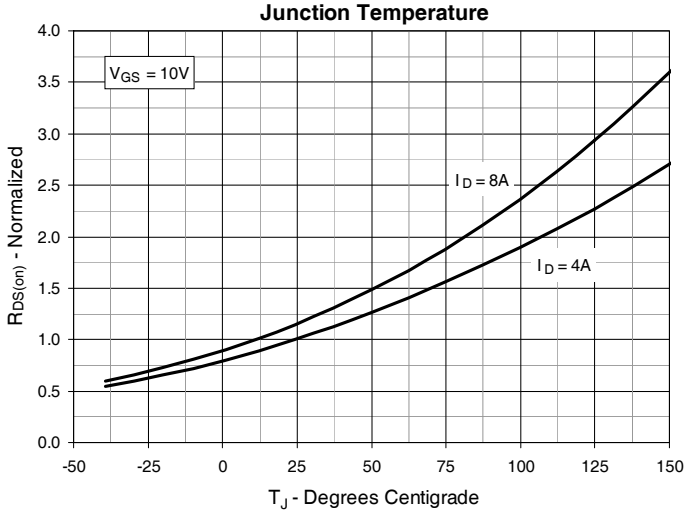

Fig. 5. $R_{DS(on)}$ Normalized to I_D = 4A Value vs. Drain Current

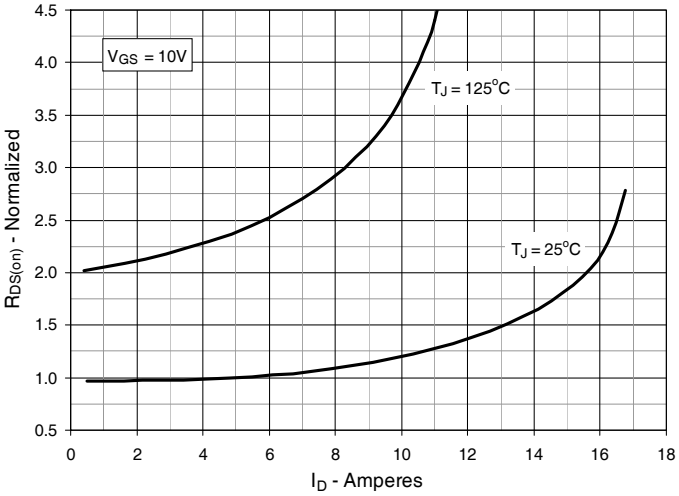

Fig. 6. Maximum Drain Current vs. Case Temperature

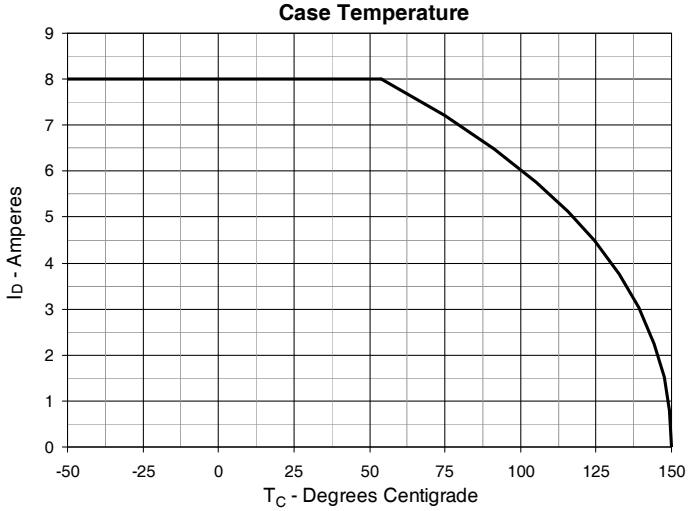

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Fig. 7. Input Admittance

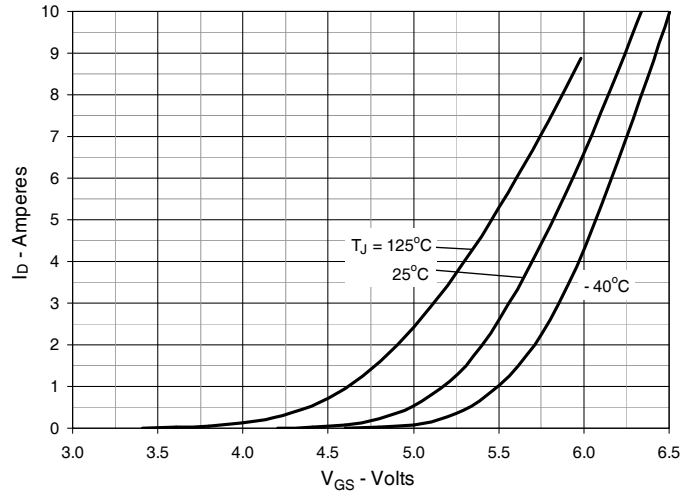


Fig. 8. Transconductance

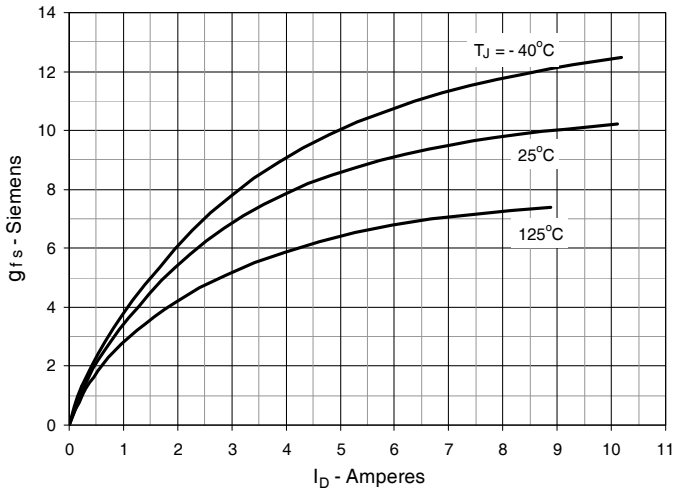


Fig. 9. Forward Voltage Drop of Intrinsic Diode

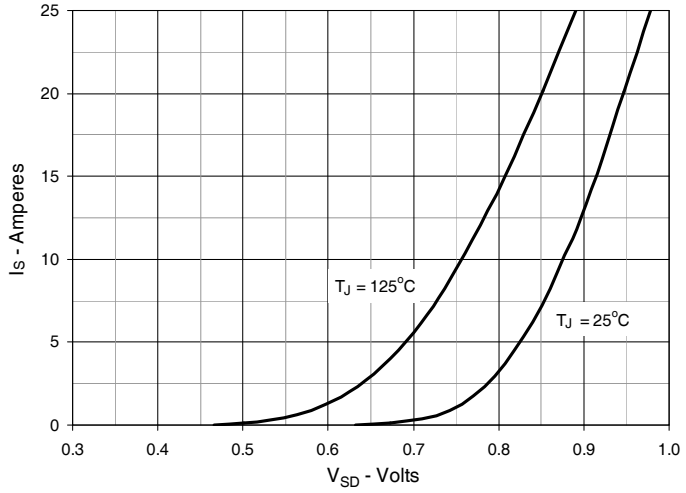


Fig. 10. Gate Charge

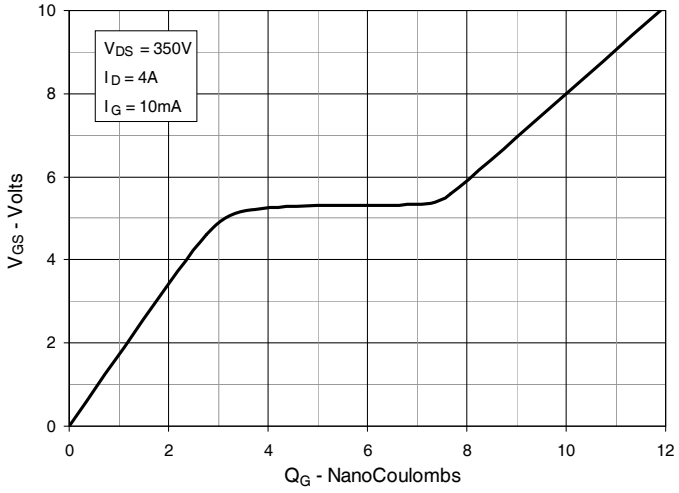


Fig. 11. Capacitance

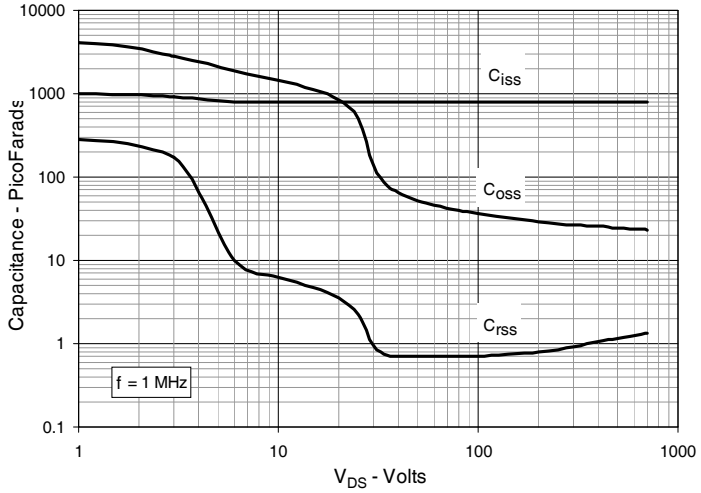
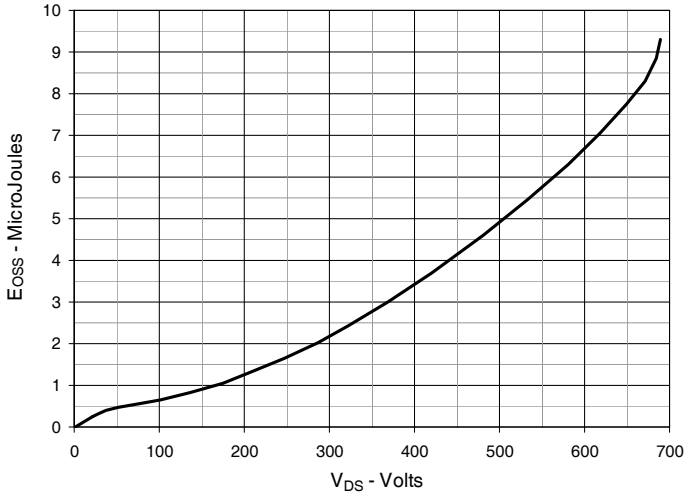


Fig. 12. Output Capacitance Stored Energy



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 13. Forward-Bias Safe Operating Area

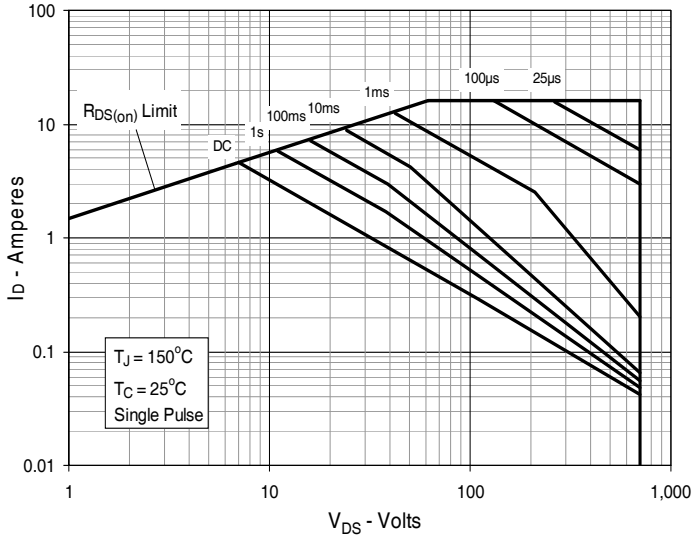
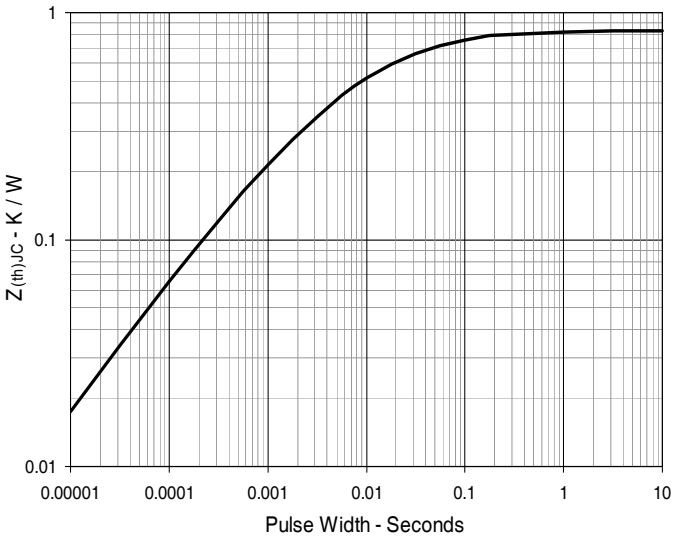


Fig. 14. Maximum Transient Thermal Impedance



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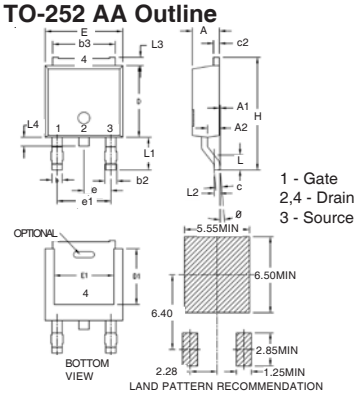
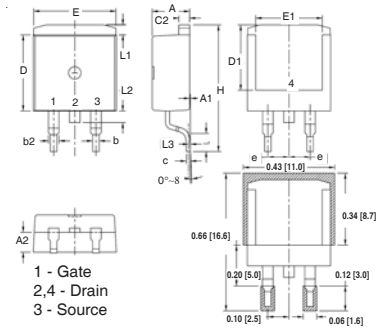
TO-252 AA Outline



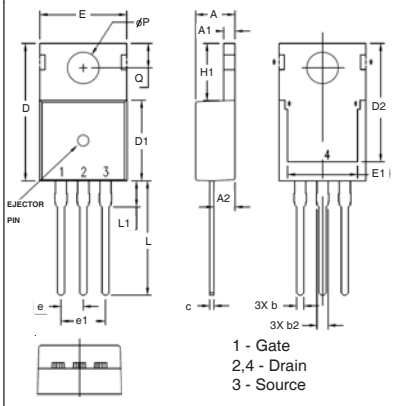
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.086	.094	2.19	2.38
A1	0	.005	0	0.12
A2	.038	.046	0.97	1.17
b	.025	.035	0.64	0.89
b2	.030	.045	0.76	1.14
b3	.200	.215	5.08	5.46
c	.018	.024	0.46	0.61
c2	.018	.023	0.46	0.58
D	.235	.245	5.97	6.22
D1	.180	.205	4.57	5.21
E	.250	.265	6.35	6.73
E1	.170	.205	4.32	5.21
e	.090 BSC		2.28 BSC	
e1	.180 BSC		4.57 BSC	
H	.370	.410	9.40	10.42
L	.055	.070	1.40	1.78
L1	.100	.115	2.54	2.92
L2	.020 BSC		0.50 BSC	
L3	.025	.040	0.64	1.02
L4	.025	.040	0.64	1.02
θ	0°	10°	0°	10°

TO-263 Outline



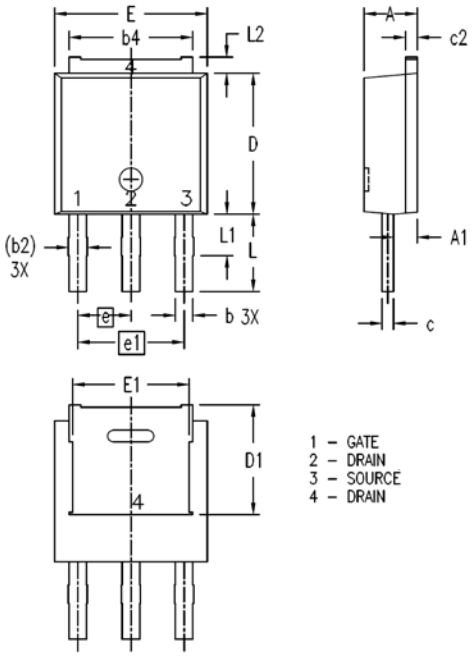
SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
e	.100 BSC		2.54 BSC	
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
L3	.010 BSC		0.254 BSC	

TO-220 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20

TO-251 OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.087	.094	2.20	2.40
A1	.032	.048	0.82	1.22
b	.026	.034	0.66	0.86
(b2)	.030	.035	0.76	0.88
b4	.198	.222	5.04	5.64
c	.018	.024	0.45	0.60
c2	.016	.024	0.40	0.60
D	.232	.248	5.90	6.30
(D1)	.179	.195	4.55	4.95
E	.252	.268	6.40	6.80
(E1)	.191	.207	4.85	5.25
e	.090 BSC		2.28 BSC	
e1	.180 BSC		4.57 BSC	
L	.126	.138	3.20	3.50
L1	.063	.079	1.60	2.00
L2	.020	.035	0.50	0.90

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